



Switched Low Noise Amplifier 800 - 1000 MHz



Features

- High Gain State:
 - Gain: 16dB, Noise Figure: 1.6dB
 - Input IP₃: +3dBm (@2.7V, 25mA)
- Low Gain State:
 - Insertion Loss: 5dB, Input IP₃: +24dBm
- Single Supply: +2.7 to +5 VDC
- Low Cost MSOP-8 Plastic Package
- Adjustable current: 10 to 30 mA with external resistor

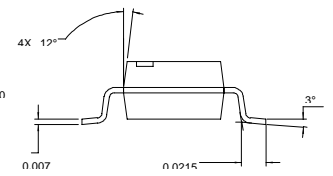
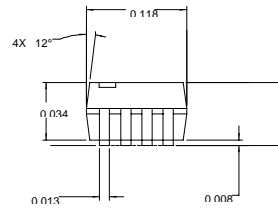
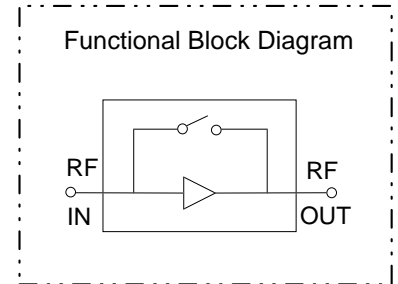
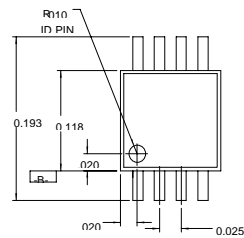
Description

M/A-COM's AM55-0016 is a high dynamic range, switchable low noise amplifier in a low cost, MSOP 8-lead, surface mount, plastic package. The design utilizes a patented switching technique to provide a low insertion loss, high input IP₃ bypass state in parallel with the high gain, low noise state. The LNA employs external input matching to obtain optimum noise figure performance and operating frequency flexibility. The AM55-0016 also features flexible biasing to control the current consumption vs. dynamic range trade-off. Its current can be controlled over a range of 10 mA to 30 mA with an external resistor.

Typical applications include receiver front ends in cellular band CDMA handsets. It is also useful as a switched gain block, buffer or driver in portable cellular systems.

The AM55-0016 is fabricated using a low-cost 0.5-micron gate length GaAs MESFET process. The process features full passivation for increased performance and reliability.

MSOP-8



Ordering Information

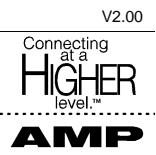
| Part Number | Package |
|--------------|-----------------------------|
| AM55-0016 | MSOP 8-Lead Plastic Package |
| AM55-0016TR | Forward Tape and Reel* |
| AM55-0016RTR | Reverse Tape and Reel* |
| AM55-0016SMB | Designer's Kit |

* If specific reel size is required, consult factory for part number.

Electrical Specifications¹ T_A = +25°C, Z₀=50Ω, F=881 MHz, P_{IN}= -30 dBm, V_{DD}=2.7 V, I_{DD}=10 mA

| Parameter | Test Conditions | Units | Min. | Typ. | Max. |
|--|---|-------|------|-------|------|
| HIGH GAIN STATE , Voltage control = 2.7 volts | | | | | |
| Gain | | dB | — | 16 | — |
| Noise Figure | | dB | — | 1.6 | 1.8 |
| Input IP ₃ | I _{DD} = 10 mA, V _{DD} = 2.7V | dBm | — | -2 | — |
| | I _{DD} = 25 mA, V _{DD} = 2.7V | dBm | — | +3 | — |
| Input VSWR / Output VSWR | | — | — | 2.0:1 | — |
| Reverse Isolation | | dB | — | 32 | — |
| LOW GAIN STATE , Voltage control = 0 volts | | | | | |
| Insertion Loss | I _{DD} = 100 μA | dB | — | 5 | — |
| Input IP ₃ | | dBm | — | +24 | — |
| Input VSWR | | — | — | 2.3:1 | — |
| Output VSWR | | — | — | 2.0:1 | — |

1. Refer to *Typical Performance Data* for performance versus frequency and bias.



Absolute Maximum Ratings¹

| Parameter | Absolute Maximum |
|----------------------------------|------------------|
| V _{DD} | +6 VDC |
| Input Power | 0 dBm |
| Current | 30 mA |
| Channel Temperature ² | +150°C |
| Operating Temperature | -40°C to +85°C |
| Storage Temperature | -65°C to +150°C |

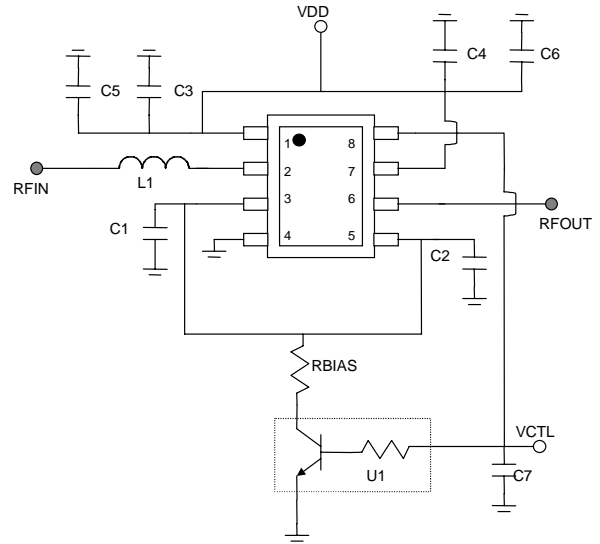
1. Exceeding any one or combination of these limits may cause permanent damage.
2. Typical thermal resistance (θ_{jc}) = +99°C/W.

External Circuitry Parts List¹

| Part | Value | Purpose |
|------------|------------|-------------------------|
| C1, C2 | 1000 pF | Source Bypass |
| C3, C4 | 47 pF | By-Pass |
| C5, C6, C7 | 10 nF | By-Pass |
| L1 | 22 nH | Tuning |
| RBIAS | see note 2 | Source Bias Resistor |
| U1 | UMH9N | Dual Bipolar Transistor |

1. All external circuitry parts are readily available, low cost surface mount components (0.040 inches x 0.020 inches or 0.060 inches x 0.030 inches).
2. RBIAS is chosen to set the desired current,
 For: $I_{dd} \sim 10$ mA, R1 = 75 ohms;
 $I_{dd} \sim 20$ mA, R1 = 25 ohms;
 $I_{dd} \sim 30$ mA, R1 = 9 ohms.

External Circuitry

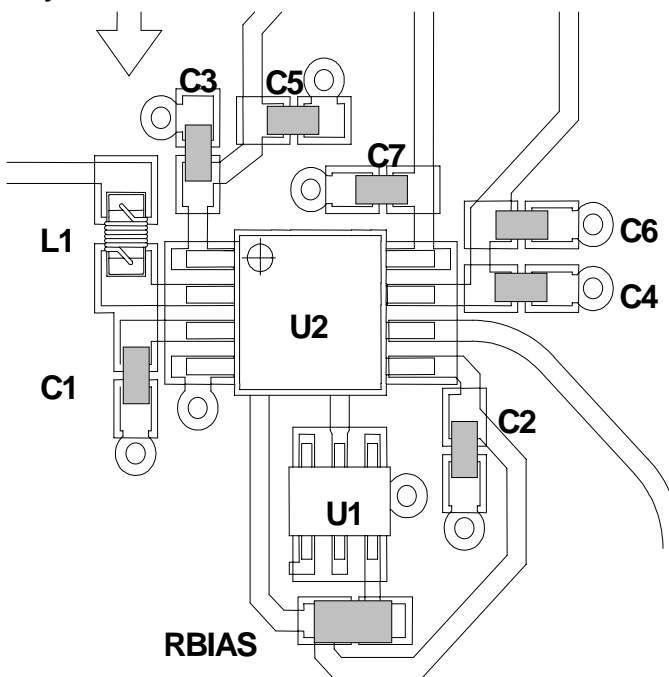


Pin Configuration

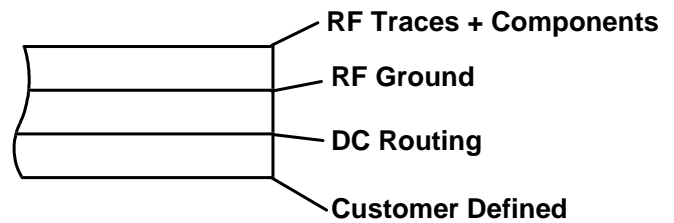
| Pin No. | Pin Name | Description |
|---------|----------|------------------------|
| 1 | VDD1 | Stage 1 Supply Voltage |
| 2 | IN | RF Input |
| 3 | VS1 | Stage 1 Source |
| 4 | GND | RF and DC Ground |
| 5 | VS2 | Stage 2 Source |
| 6 | OUT | RF Output |
| 7 | VDD2 | Stage 2 Supply Voltage |
| 8 | VCTL | Switch Control Voltage |

Recommended PCB Configuration

Layout View



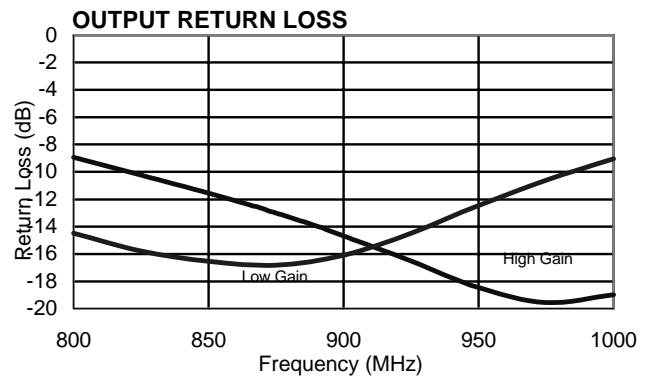
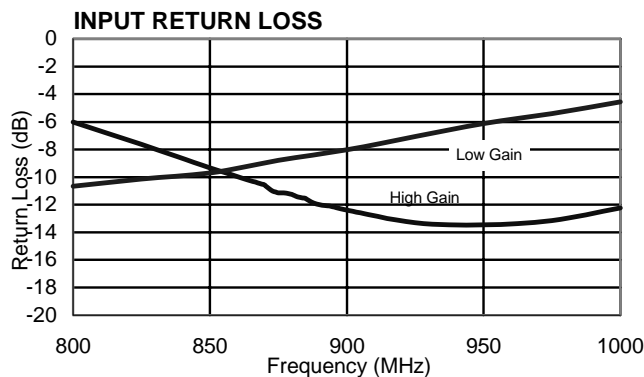
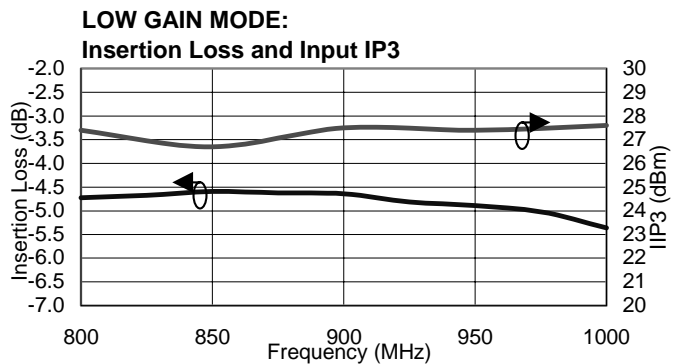
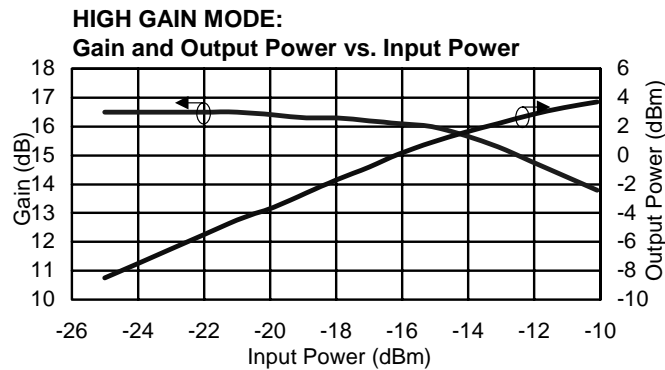
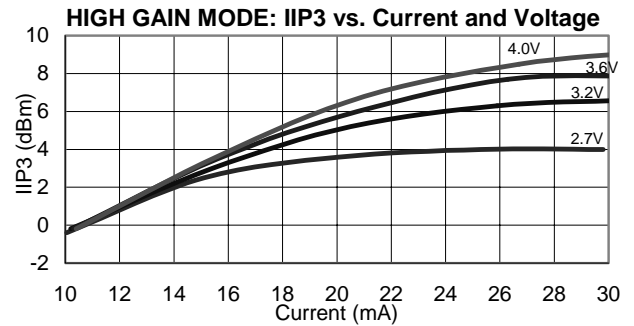
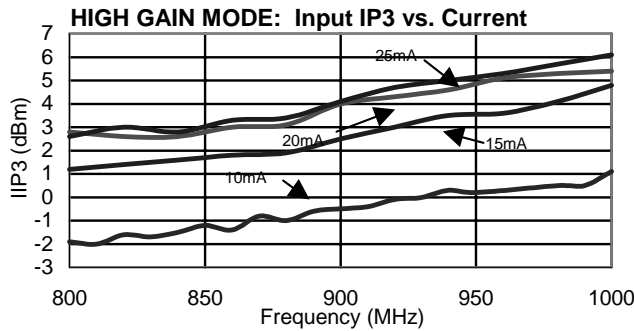
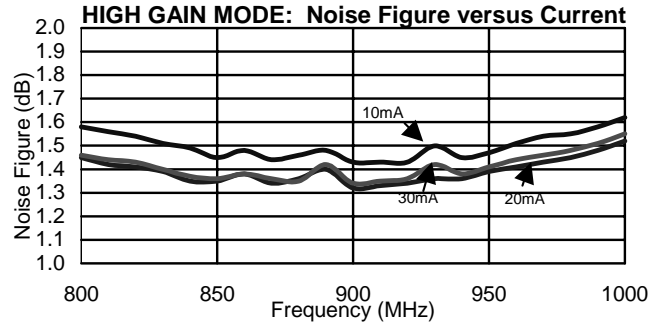
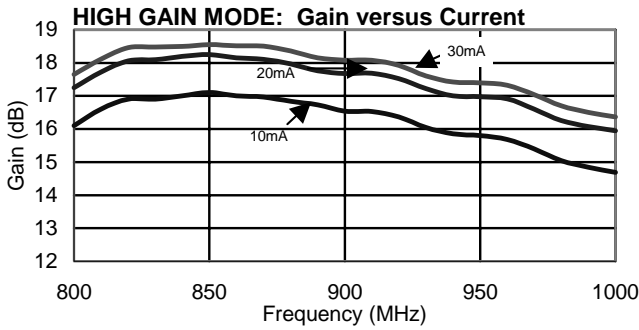
Cross Section View



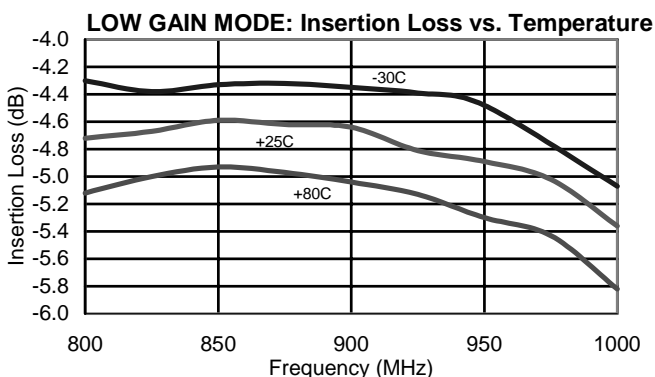
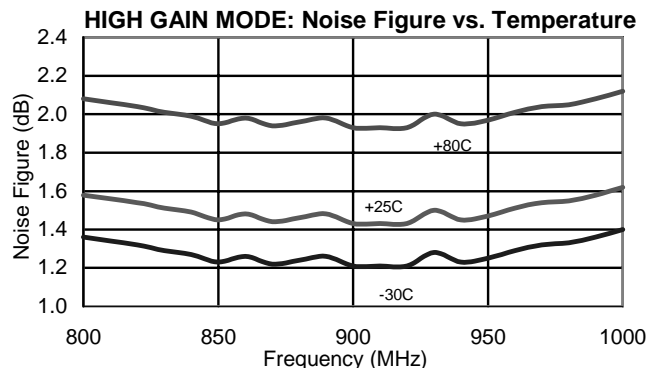
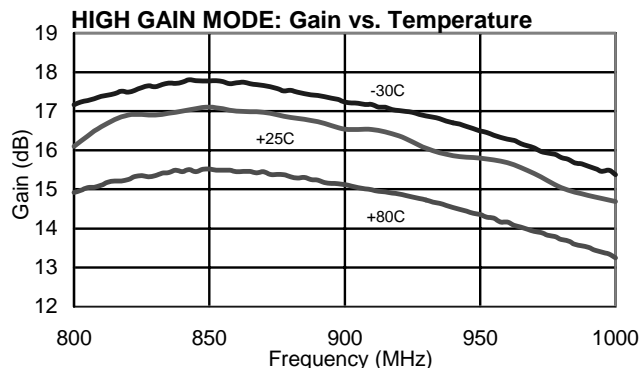
The PCB dielectric between RF traces and RF ground layers should be chosen to reduce RF discontinuities between 50 Ω lines and package pins. M/A-COM recommends an FR-4 dielectric thickness of 0.008" (0.2 mm) yielding a 50 Ω line width of 0.015" (0.38 mm). The recommended metalization thickness is 1 ounce copper.

Typical Performance Data

Test Conditions: $T_A = +25^\circ\text{C}$, $Z_0 = 50\Omega$, $V_{DD} = 2.7\text{V}$, $I_{DD} = 10\text{mA}$ unless otherwise specified.



Typical Performance Data (continued)



Designer's Kit AM55-0016SMB

The AM55-0016SMB Designer's Kit allows for immediate evaluation of M/A-COM's AM55-0016. The Designer's Kit includes an AM55-0016, an evaluation board and a floppy disk containing typical performance data and a DXF file of the recommended PCB layout. The evaluation board consists of the recommended external surface mount circuitry, RF connectors and a DC multi-pin connector, all mounted to a multi-layer FR-4 PCB. The AM55-0016SMB evaluation PCB is illustrated below with all functional ports labeled.

Evaluation PCB + RF Connector Losses

| Port Reference | Approximate RF Loss |
|----------------|---------------------|
| RF IN | 0.15 dB @ 900 MHz |
| RF OUT | 0.15 dB @ 900 MHz |

The DC connector on the Designer's Kit PCB allows convenient DC line access. This is accomplished by one or more of the following methods:

1. A mating female multi-pin connector (Newark Electronics Stock # 46F-4658, not included).
2. Wires soldered to the necessary pins (not included).
3. Clip leads (not included).

AM55-0016 Evaluation Board

